

2A, 600V N-Channel MOSFET

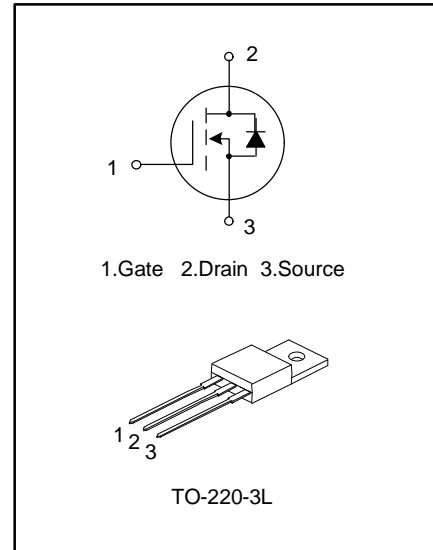
GENERAL DESCRIPTION

SVD2N60T is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary S-Rin™ structure DMOS technology. The improved planar stripe cell and the improved guarding ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.

FEATURES

- * 2A,600V,RDS(on)(typ.)=4.0Ω@VGS=10V
- * Low gate charge
- * Low Crss
- * Fast switching
- * Improved dv/dt capability



ORDERING SPECIFICATIONS

Part No.	Package	Marking	Shipping
SVD2N60T	TO-220-3L	SVD2N60T	50Unit/Tube

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	600	V
Gate-Source Voltage	VGS	±30	V
Drain Current	ID	2.0	A
Drain Current Pulsed	IDM	8	A
Power Dissipation(Tc=25°C)	PD	44	W
-Derate above 25°C		0.22	W/°C
Single Pulsed Avalanche Energy (Note 1)	EAS	120	mJ
Repetitive Avalanche Energy	EAR	5.4	mJ
Operation Junction Temperature	TJ	-55~+150	°C
Storage Temperature	Tstg	-55~+150	°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	2.87	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	100	°C/W

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BVDSS	V _{GS} =0V, I _D =250μA	600	--	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V	--	--	1.0	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =1.0A	--	4.0	4.6	Ω
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	--	320	380	pF
Output Capacitance	C _{oss}		--	30	45	
Reverse Transfer Capacitance	C _{rss}		--	3	5.6	
Turn-on Delay Time	t _{d(on)}	V _{DD} =300V, I _D =2.0A, R _G =25Ω (Note 2,3)	--	13	30	ns
Turn-on Rise Time	t _r		--	12	60	
Turn-off Delay Time	t _{d(off)}		--	73	100	
Turn-off Fall Time	t _f		--	14.3	70	
Total Gate Charge	Q _g	V _{DS} =480V, I _D =2.0A, V _{GS} =10V (Note 2,3)	--	9.3	13	nC
Gate-Source Charge	Q _{gs}		--	2.0	--	
Gate-Drain Charge	Q _{gd}		--	3.3	--	

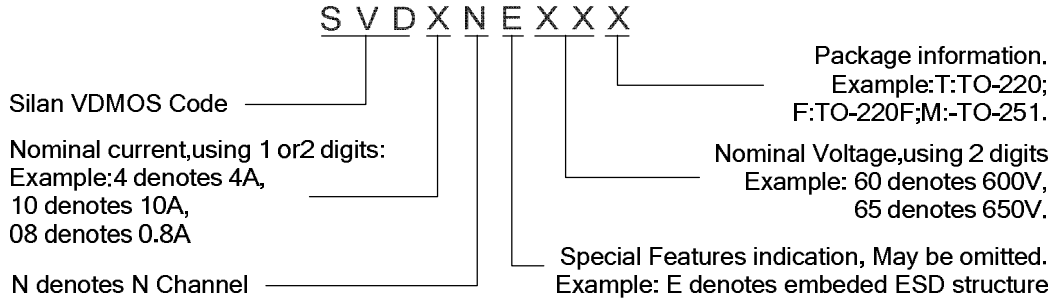
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Parameter	Symbol	Test conditions	Min.	Typ.	Max	Unit
Continuous Source Current	I _S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	2	A
Pulsed Source Current	I _{SM}		--	--	8.0	
Diode Forward Voltage	V _{SD}	I _S =2.0A, V _{GS} =0V	--	--	1.4	V
Reverse Recovery Time	T _{rr}	I _S =2.0A, V _{GS} =0V, dI _F /dt=100A/μS	--	230	--	ns
Reverse Recovery Charge	Q _{rr}		--	1.0	--	μC

Notes:

1. L=56mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25Ω, starting T_J=25°C;
2. Pulse Test: Pulse width ≤300μs, Duty cycle≤2%;
3. Essentially independent of operating temperature.

NOMENCLATURE



TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

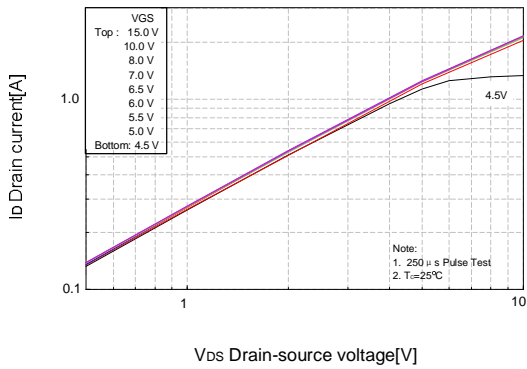


Figure 2. Transfer Characteristics

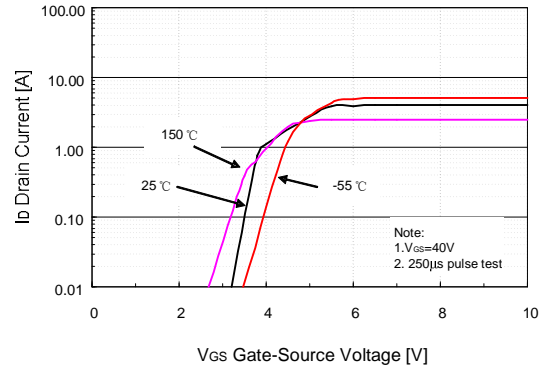


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

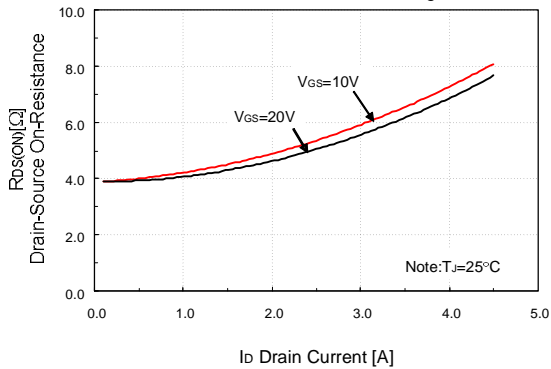
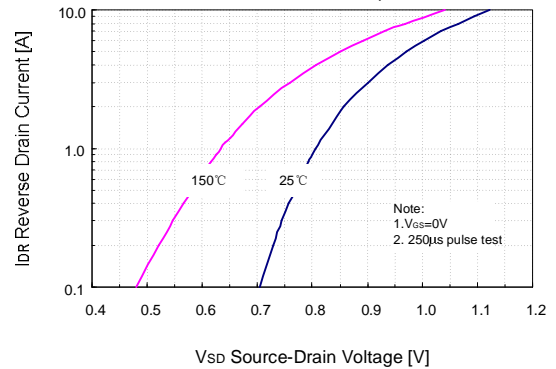


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



TYPICAL CHARACTERISTICS (continued)

Figure 5. Capacitance Characteristics

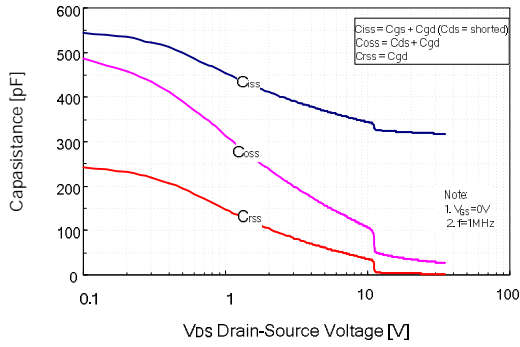


Figure 6. Gate Charge Characteristics

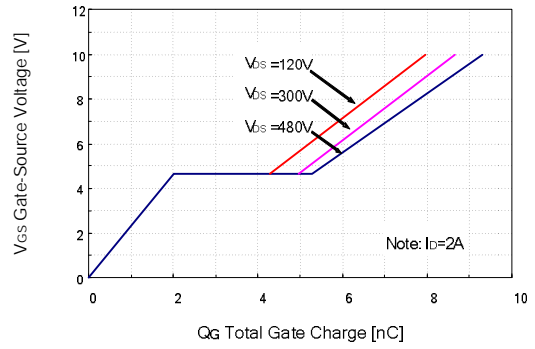


Figure 7. Breakdown Voltage Variation vs. Temperature

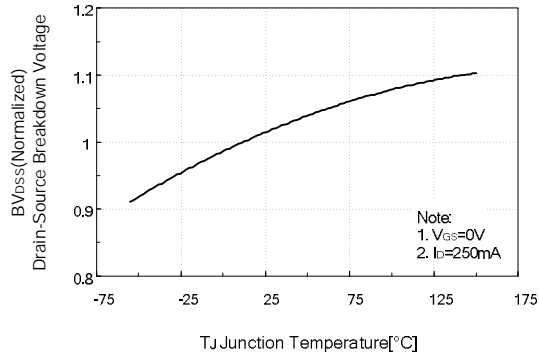
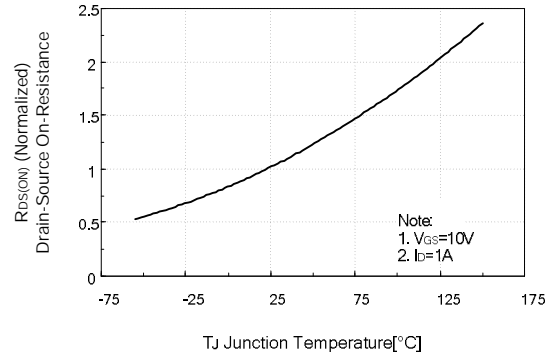
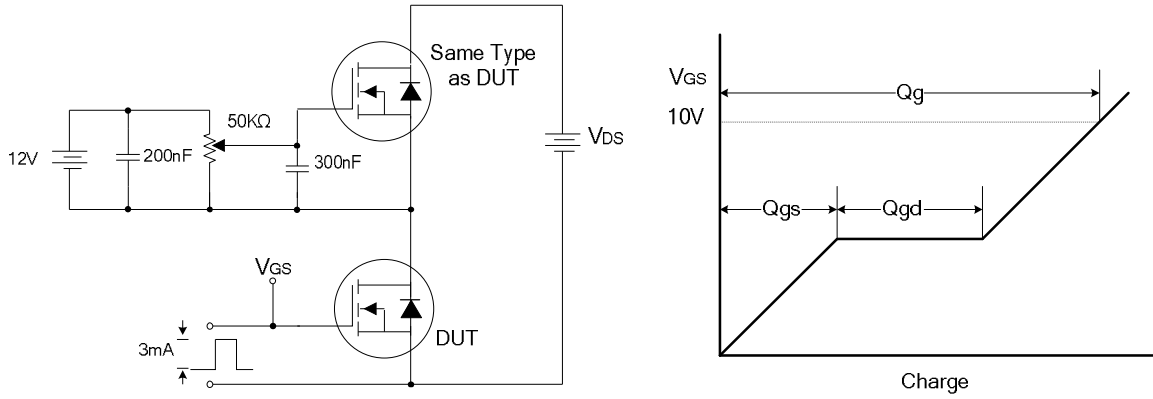


Figure 8. On-resistance Variation vs Temperature

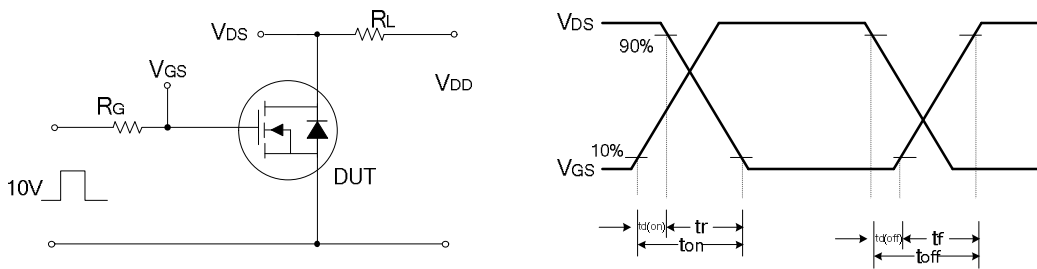


TYPICAL TEST CIRCUIT

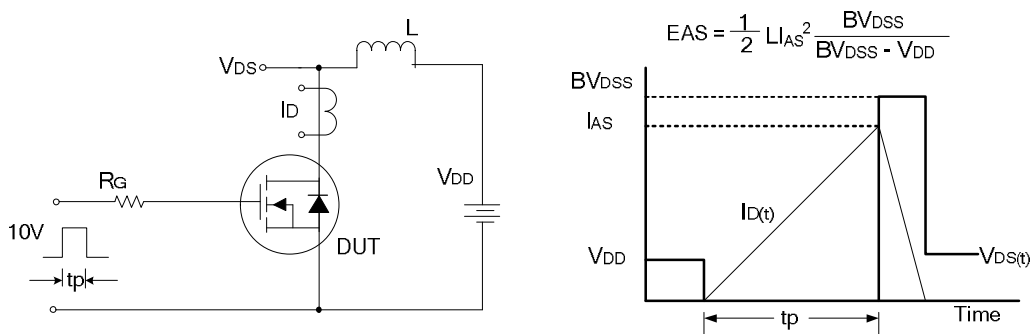
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



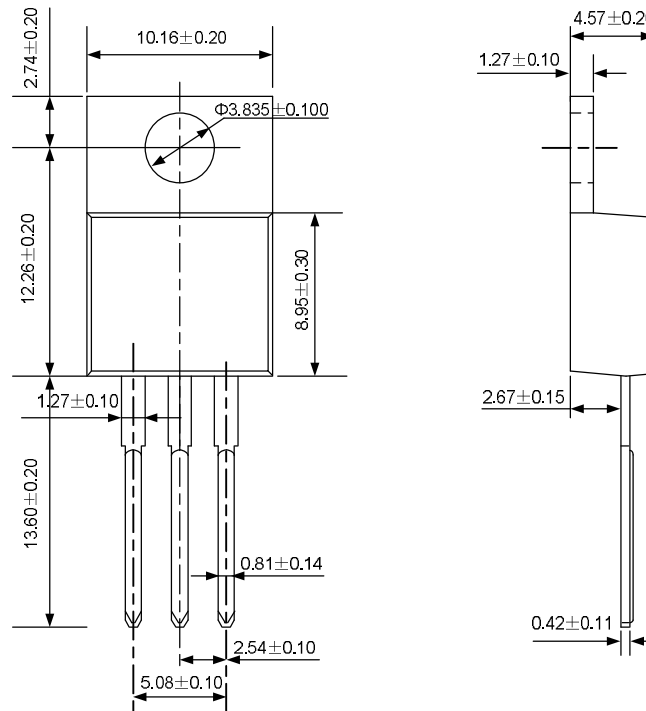
Unclamped Inductive Switching Test Circuit & Waveform



PACKAGE OUTLINE

TO-220-3L(One)

UNIT: mm



TO-220-3L (Two)

UNIT: mm

